

## N-Channel Enhancement Mode Power MOSFET

### DESCRIPTION

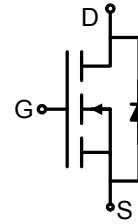
The HM3400D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### GENERAL FEATURES

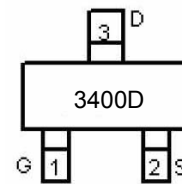
- $V_{DS} = 30V, I_D = 5.0A$   
 $R_{DS(ON)} < 52m\Omega @ V_{GS}=2.5V$   
 $R_{DS(ON)} < 36m\Omega @ V_{GS}=4.5V$   
 $R_{DS(ON)} < 32m\Omega @ V_{GS}=10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

### Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

### Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3400D	HM3400D	SOT-23-3L	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	±12	V
Drain Current-Continuous	$I_D$	5.0	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	1.4	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	1.0	°C/W
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### Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V

Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.6	0.9	1.4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	-	46	52	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.9A	-	30	36	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =2.9A	-	26	32	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =2.9A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	623	-	PF
Output Capacitance	C <sub>OSS</sub>		-	99	-	PF
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	77	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =2.9A V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω	-	3.3	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	4.8	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	26	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =5.0A, V <sub>GS</sub> =4.5V	-	9.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =2.9A	-	0.75	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	2.9	A

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

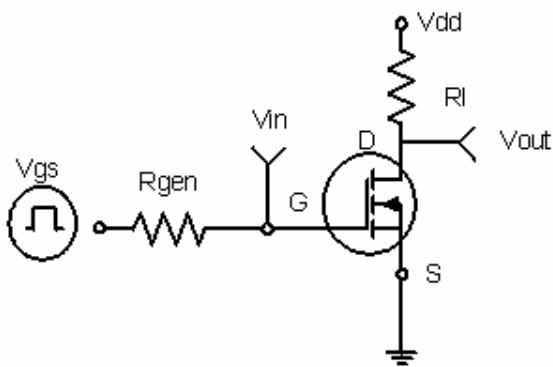


Figure 1: Switching Test Circuit

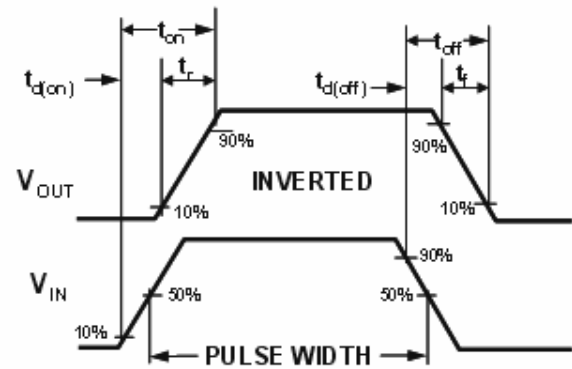
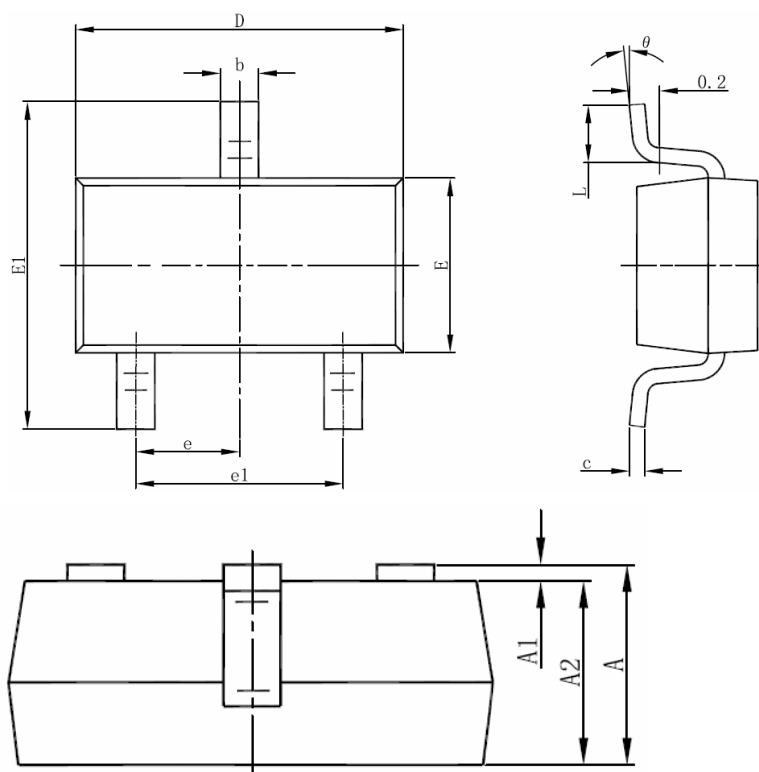


Figure 2: Switching Waveforms

## SOT-23-3L PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

### NOTES

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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